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Form PTO-1449 (Woodward)	U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No. 30848/40704	Serial No. 10/516,384
INFORMATION DISCLOSURE STATEMENT		Applicant Gogolides et al.	
		Filing Date May 30, 2003	Group

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)		
STL		"Double Layer Resist System for High Resolution Lithography", Hatzakis et al., Proc. Microcircuit Engng. Lausanne, 1981, pp. 386-396
		"Linear Hybrid Polymer Building Blocks: Methacrylate-Functionalized Polyhedral Oligomeric Silsesquioxane Monomers and Polymers", Lichtenhan et al., Macromolecules 28, 1995, pp. 8435-8437
		"Extension of 248 nm Optical Lithography: A Thin Film Imaging Approach", Lin et al., SPIE Vol. 3333, 1998, pp. 278-288
		"Outlook for 157-nm Resist Design", Kunz et al., SPIE Vol. 3678, March 1999, pp. 13-20
		"Incorporation of Polyhedral Oligosilsesquioxane in Chemically Amplified Resists to Improve Their Reactive Ion Etching Resistance", Wu et al., J. Vac. Sci. Technol. B 19(3), May/June 2001, pp. 851-855
		"Novel CA Resists with Photoacid Generator in Polymer Chain", Wu et al., SPIE Vol. 4345, 2001, pp. 521-527
		"Novel Positive-Tone Chemically Amplified Resists with Photoacid Generator in the Polymer Chains", Wu et al., Adv. Mater 13, No. 9, May 2001, pp. 670-672
		"Silicon-Containing Resists for 157 nm Applications", Sooriyakumaran et al., SPIE Vol. 4345, 2001, pp. 319-326
		"Recent Advances in Resists for 157 nm Microlithography", Trinque et al., J. Vac. Sci. Technol. B 20(2), March/April 2002, pp. 531-536
		International Search Report in PCT/GB03/00018 dated September 23, 2003

Examiner <i>S. J. Lu</i>	Date Considered <i>9-30-'07</i>
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	